

## GJ8550

### PNP EPITAXIAL TRANSISTOR

#### Description

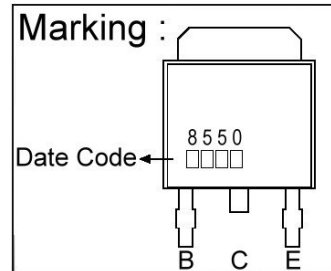
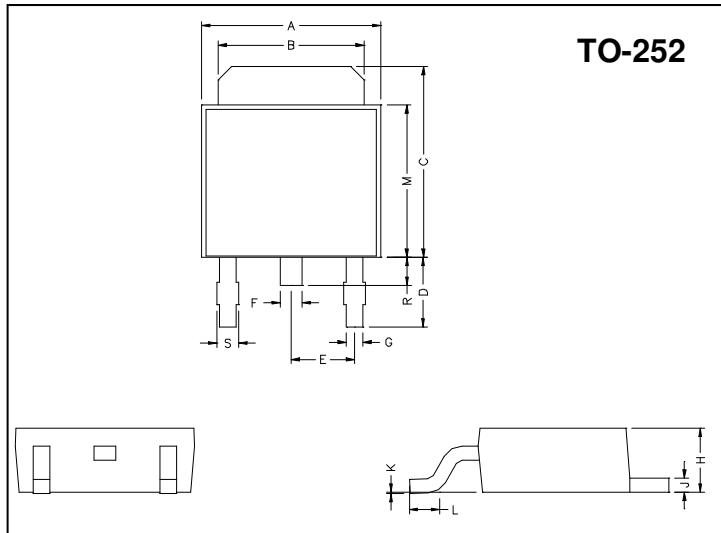
The GJ8550 is designed for use in 2W output amplifier of portable radios in class B push-pull operation.

#### Features

\*High Collector current (IC: 1.5A)

\*Complementary to GJ8050

#### Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.40	6.80	G	0.50	0.70
B	5.20	5.50	H	2.20	2.40
C	6.80	7.20	J	0.45	0.55
D	2.40	3.00	K	0	0.15
E	2.30 REF.		L	0.90	1.50
F	0.70	0.90	M	5.40	5.80
S	0.60	0.90	R	0.80	1.20

#### Absolute Maximum Ratings (Ta = 25°C, unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	VCBO	-40	V
Collector to Emitter Voltage	VCEO	-25	V
Emitter to Base Voltage	VEBO	-6	V
Collect Current	IC	-1.5	A
Base Current	IB	-0.5	A
Junction Temperature	Tj	+150	°C
Storage Temperature Range	TSTG	-55 ~ +150	°C
Total Power Dissipation	PD	1.25	W

#### Electrical Characteristics (Ta = 25°C, unless otherwise specified)

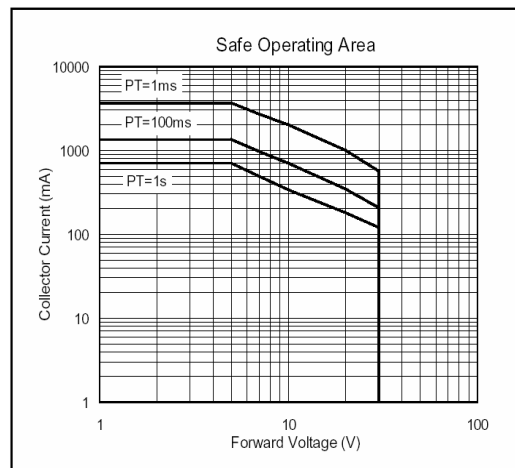
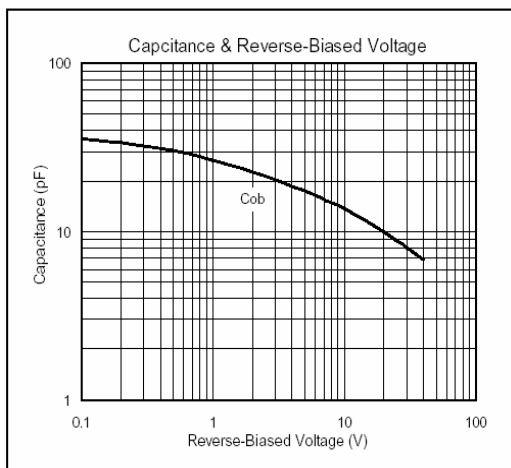
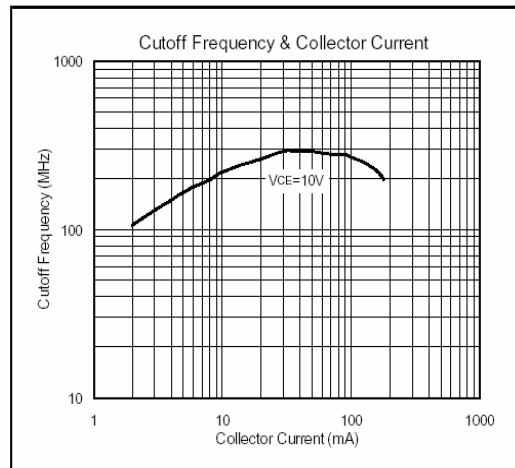
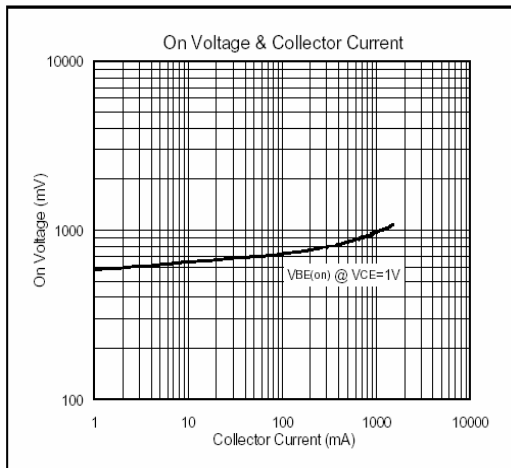
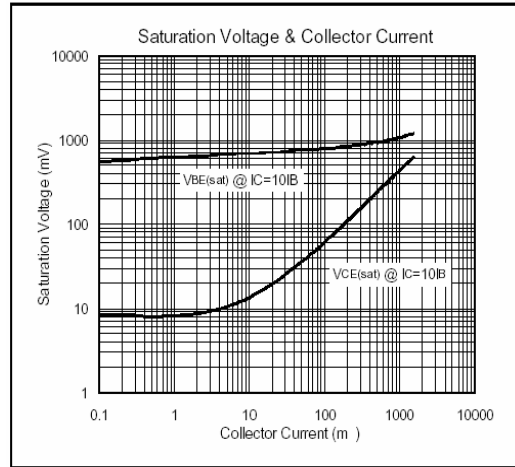
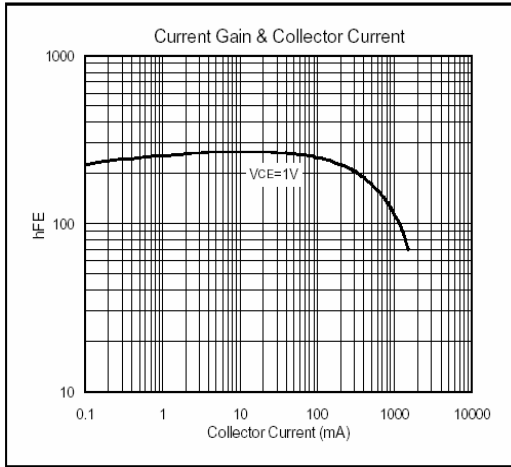
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	-40	-	-	V	Ic=-100uA
BVCEO	-25	-	-	V	Ic=-2mA
BVEBO	-6	-	-	V	IE=-100uA
ICBO	-	-	-100	nA	VCB=-35V
IEBO	-	-	-100	nA	VBE=-6V
*VCE(sat)	-	-	-0.5	V	Ic=-800mA, Ib=-80mA
*VBE(sat)	-	-	-1.2	V	Ic=-800mA, Ib=-80mA
*VBE(on)	-	-	-1	V	VCE=-1V, Ic=-10mA
*hFE1	45	-	-		VCE=-1V, Ic=-5mA
*hFE2	120	-	500		VCE=-1V, Ic=-100mA
*hFE3	40	-	-		VCE=-1V, Ic=-800mA
fT	100	-	-	MHz	VCE=-10V, Ic=-50mA, f=100MHz
Cob	-	9	-	pF	VCB=-10V, IE=0, f=1MHz

\* Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%

#### Classification Of hFE2

Rank	C	D	E
Range	120 ~ 200	160 ~ 300	250 ~ 500

## Characteristics Curve



**Important Notice:**

- All rights are reserved. Reproduction in whole or in part is prohibited without the prior written approval of GTM.
- GTM reserves the right to make changes to its products without notice.
- GTM semiconductor products are not warranted to be suitable for use in life-support Applications, or systems.
- GTM assumes no liability for any consequence of customer product design, infringement of patents, or application assistance.

**Head Office And Factory:**

- **Taiwan:** No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
- TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- **China:** (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China
- TEL : 86-21-5895-7671 ~ 4 FAX : 86-21-38950165